Technical Data Data Sheet 4951, Rev.A

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	45	V
Max. Average Forward	I _{F(AV)}	50% duty cycle, rectangular	7.5	Α
Current	, ,	wave form		
Max. Peak One Cycle Non-	I _{FSM}	8.3 ms, half Sine wave	140	Α
Repetitive Surge Current				
Non-Repetitive Avalanche	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 2.0 \text{A},$	13.0	mJ
Energy		L = 6.5 mH		
Repetitive Avalanche Current	I _{AR}	I _{AS} decay linearly to 0 in 1 μs	2.0	Α
		f limited by T _J max V _A =1.5V _R		
Max. Junction Temperature	TJ	-	-65 to +125	°C
Max. Storage Temperature	T _{stg}	-	-65 to +125	°C

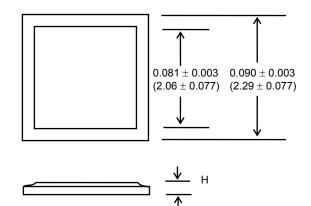
Electrical Characteristics(1):

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 7.5A, Pulse, T _J = 25 °C	0.51	V
	V_{F2}	@ 7.5A, Pulse, T _J = 125 °C	0.47	V
Max. Reverse Current	I _{R1}	@V _R = 45V, Pulse,	800	μΑ
		T _J = 25 °C		
	I_{R2}	@V _R = 45V, Pulse,	120	mA
		T _J = 100 °C		
Max. Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 °C$	430	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

(1) in SHD package

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Mechanical Dimensions: In Inches / mm



Bottom side metalization Ag - 30 kÅ minimum.

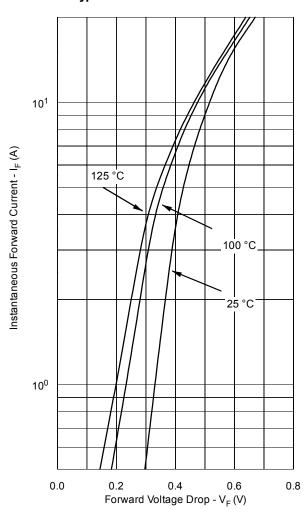
Top side metalization AI - 25 kÅ minimum or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

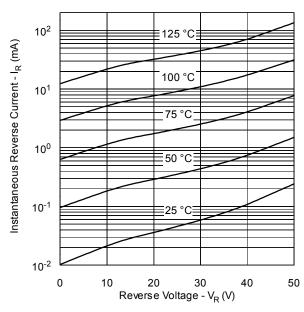
Dimension H = 0.0105 ± 0.001 (0.27 ± 0.026) for Al top; Dimension H = 0.0155 ± 0.001 (0.39 + 0.026) for Ag top.

Gold Option Available for Top and/or Bottom Metalization: Ti (1.2 kA) / Ni (1.8 kA) / Au (12kA)

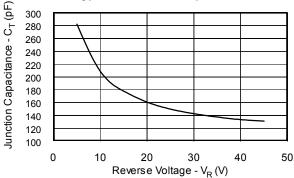
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



SD090SE45A/B/C

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